

FEATURES

- Class AB linear GaAsFET design
- Instantaneous wide bandwidth
- Designed for EMI/RFI, lab, and general communication applications
- Suitable for all single channel modulation standards
- Rack mounted system
- Local LCD & remote flexible interfaces
- High reliability and ruggedness


ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	26.5 - 40.0 GHz	
Power Output	10 Watt Min	Saturated CW
Power Output at P1dB GCP	10 Watt Typ	
Power Gain	40 dB Min	
Power Gain Flatness	6.0 dB p-p Max	
Input Return Loss	-10 dB Max	Relative to 50 Ω
Noise Figure	12 dB Max	
Harmonics	-20 dBc Typ	At rated Pout
Spurious	-60 dBc Max	Non-harmonics
Operating Voltage	100 - 240 VAC	
Power Consumption	360 Watt Max	At rated Pout
Input Power Protection	+3 dBm Max	<10Sec without damage
Load VSWR Protection	∞ : 1	<1 Minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Ambient Temperature	0 to +50 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions W x H x D	19 x 7 x 22 inch (483 x 178 x 580 mm)	10U
Weight	30 Kg.	
RF Connectors In/Out	2.9 mm (K / air type) Female	
Gate Control	BNC Female	
AC Power / Interface Connector	IEC 60320-C14 / 9-Pin D-Sub	
Cooling	Built in Fan Cooling	
Standard Digital Monitor & Control: FWD, REV, VSWR, GAIN, ALC, V & I, TEMP	Ethernet RJ-45 TCP/IP, RS422/485, USB, GPIB Interface	